



ELECTRONICS, INC.
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NTE92 (NPN) & NTE93 (PNP) Silicon Complementary Transistors Hi-Fi Power Amp, Audio Output

Absolute Maximum Ratings: ($T_A = +25^\circ\text{C}$ unless otherwise specified)

Collector-Base Voltage, V_{CBO}	200V
Collector-Emitter Voltage, V_{CEO}	200V
Emitter-Base Voltage, V_{EBO}	6V
Collector Current, I_C	15A
Base Current, I_B	5A
Collector Power Dissipation ($T_C = +25^\circ\text{C}$), P_C	150W
Junction Temperature, T_J	$+150^\circ\text{C}$
Storage Temperature Range, T_{stg}	-55° to $+150^\circ\text{C}$

Note 1. Matched complementary pairs are available upon request (NTE93MCP). Matched complementary pairs have their gain specification (h_{FE}) matched to within 10% of each other.

Electrical Characteristics: ($T_A = +25^\circ\text{C}$ unless otherwise specified)

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Collector Cutoff Current	I_{CBO}	$V_{CB} = 200\text{V}$	–	–	0.1	mA
Emitter Cutoff Current	I_{EBO}	$V_{BE} = 6\text{V}$	–	–	0.1	mA
Collector-Emitter Breakdown Voltage	$V_{(BR)CEO}$	$I_C = 50\text{mA}$	200	–	–	V
DC Current Gain	h_{FE}	$V_{CE} = 4\text{V}$, $I_C = 5\text{A}$	30	120	–	
Collector-Emitter Saturation Voltage	$V_{CE(sat)}$	$I_C = 10\text{A}$, $I_B = 1\text{A}$	–	3	–	V
Transistion Frequency	f_T	$V_{CE} = 12\text{V}$, $I_E = 0.5\text{A}$	–	20	–	MHz

